

# Switching diode

## 1SS400G

### ●Applications

High frequency switching

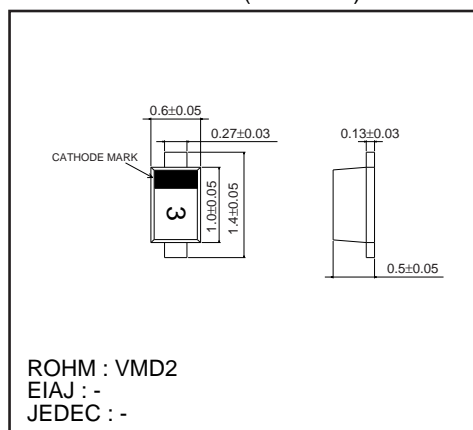
### ●Features

- 1) Ultra small mold type. (VMD2)
- 2) High reliability.

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	90	V
DC reverse voltage	$V_R$	80	V
Peak forward current	$I_{FM}$	225	mA
Mean rectifying current	$I_o$	100	mA
Surge current (1s)	$I_{surge}$	500	mA
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55~+150	°C

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	1.2	V	$I_F=100\text{mA}$
Reverse current	$I_R$	-	-	100	nA	$V_R=80\text{V}$
Capacitance between terminals	$C_T$	-	-	3.0	pF	$V_R=0.5\text{V}$ , $f=1\text{MHz}$
Reverse recovery time	$t_{rr}$	-	-	4.0	ns	$V_R=6\text{V}$ , $I_F=10\text{mA}$ , $R_L=100\Omega$

Diodes

●Electrical characteristic curves (Ta=25°C)

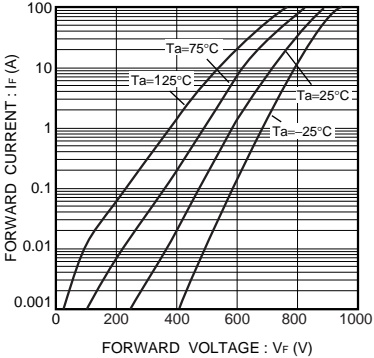


Fig.1 Forward characteristics

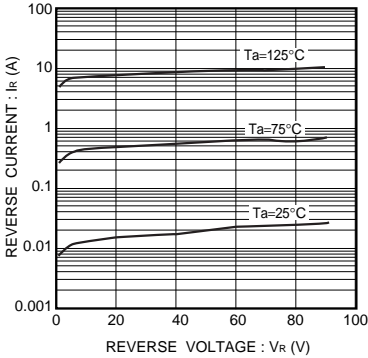


Fig.2 Reverse characteristics

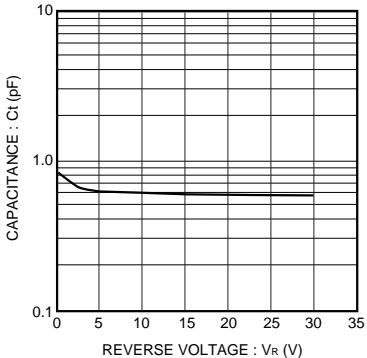


Fig.3 Characteristics